



## Technical Data Sheet

### 3mm Phototransistor T-1

#### PT204-6B

#### Features

- Fast response time
- High photo sensitivity
- Pb Free
- The product itself will remain within RoHS compliant version.

#### Descriptions

- PT204-6B is a high speed and high sensitive NPN silicon phototransistor molded in a standard 3 mm package. Due to its black epoxy the device is sensitive to infrared radiation.



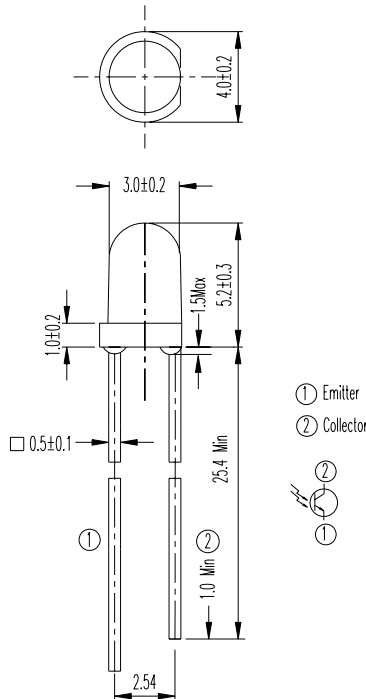
#### Applications

- Infrared applied system
- Camera
- Printer
- Cockroach catcher

#### Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
PT204-6B	Silicon	Black

**Package Dimensions**



- Notes:** 1.All dimensions are in millimeters  
 2.Tolerances unless dimensions  $\pm 0.25\text{mm}$

**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Collector-Voltage	$V_{ECO}$	5	V
Collector Current	$I_C$	20	mA
Operating Temperature	$T_{opr}$	-25 ~ +85°C	°C
Storage Temperature	$T_{stg}$	-40 ~ +85°C	°C
Lead Soldering Temperature	$T_{sol}$	260	°C
Power Dissipation at (or below) 25°C Free Air Temperature	$P_c$	75	mW

**Notes:** \*1:Soldering time  $\leq 5$  seconds.

**Electro-Optical Characteristics (Ta=25°C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Collector – Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=100\ \mu A$ $E_e=0mW/cm^2$	30	---	---	V
Emitter-Collector Breakdown Voltage	$BV_{ECO}$	$I_E=100\ \mu A$ $E_e=0mW/cm^2$	5	---	---	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2mA$ $E_e=1mW/cm^2$	---	---	0.4	V
Rise Time	$t_r$	$V_{CE}=5V$ $I_C=1mA$	---	15	---	$\mu S$
Fall Time	$t_f$	$RL=1000\ \Omega$	---	15	---	
Collector Dark Current	$I_{CEO}$	$E_e=0mW/cm^2$ $V_{CE}=20V$	---	---	100	nA
On State Collector Current	$I_{C(on)}$	$E_e=1mW/cm^2$ $V_{CE}=5V$	0.7	---	5.07	mA
Wavelength of Peak Sensitivity	$\lambda_p$	---	---	940	---	nm
Rang of Spectral Bandwidth	$\lambda_{0.5}$	---	---	760-1100	---	nm

**Rankings**

Parameter	Symbol	Min	Max	Unit	Test Condition
G	$I_{C(ON)}$	0.7	1.9	mA	$V_{CE}=5V$ $E_e=1mW/c\ m^2$
H		1.14	2.6		
J		1.77	3.61		
K		2.67	5.07		

**Typical Electro-Optical Characteristics Curves**

Fig.1 Collector Power Dissipation vs. Ambient Temperature

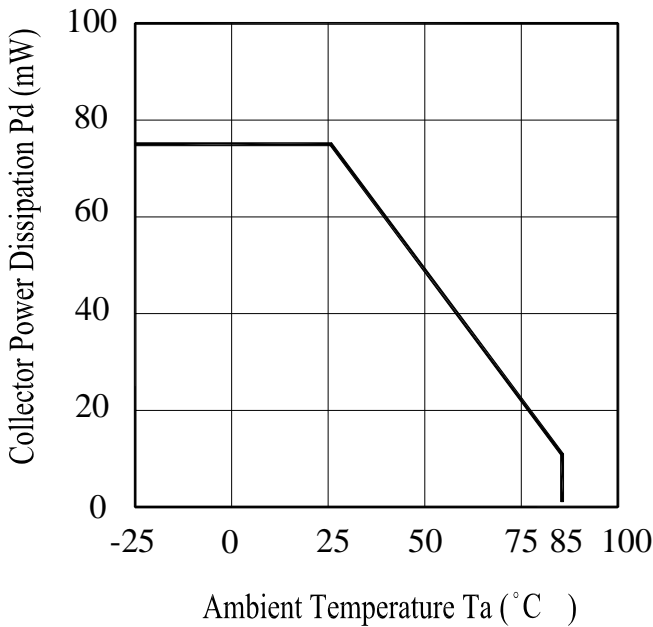


Fig.2 Spectral Sensitivity

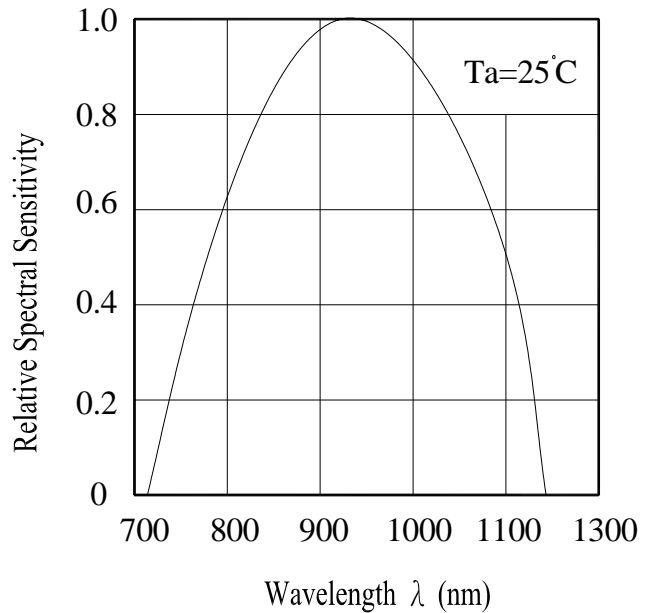


Fig.3 Relative Collector Current vs. Ambient Temperature

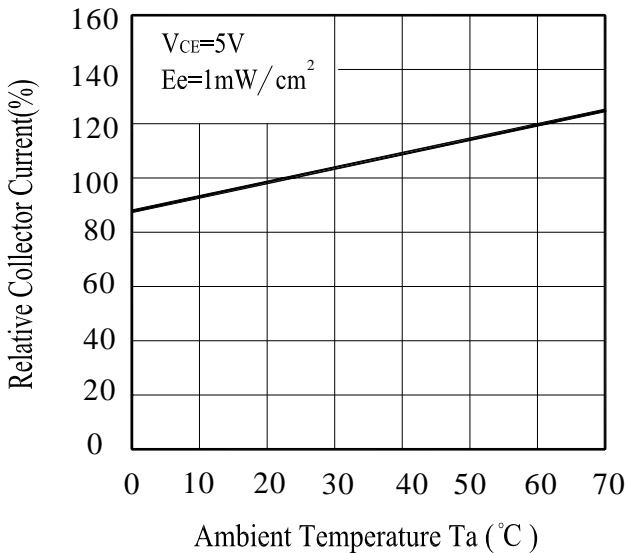
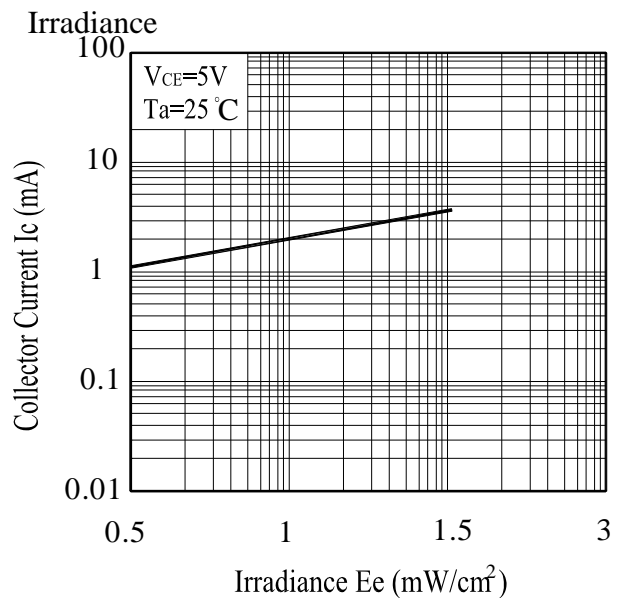


Fig.4 Collector Current vs. Irradiance



**Typical Electro-Optical Characteristics Curves**

Fig.5 Collector Dark Current vs. Ambient Temperature

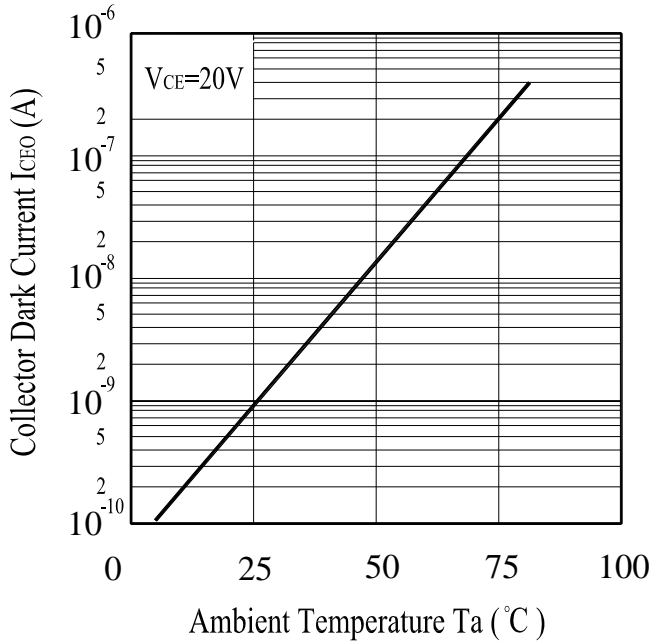
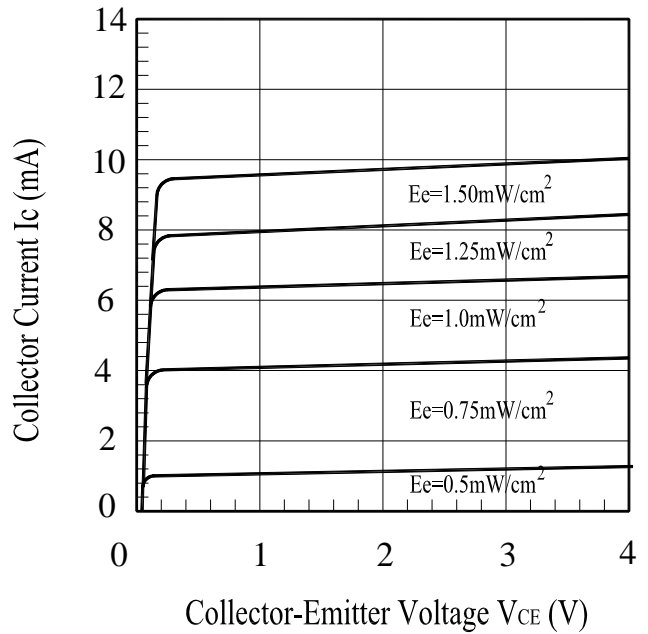


Fig.6 Collector Current vs. Collector-Emitter Voltage



**Reliability Test Item And Condition**

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP. : 260°C±5°C	10secs	22pcs	$I_{C(ON)} \leq L \times 0.8$  L : Lower Specification Limit	0/1
2	Temperature Cycle	H : +100°C    15mins ↑ 5mins ↓ L : -40°C    15mins	300Cycles	22pcs		0/1
3	Thermal Shock	H : +100°C    5mins ↑ 10secs ↓ L : -10°C    5mins	300Cycles	22pcs		0/1
4	High Temperature Storage	TEMP. : +100°C	1000hrs	22pcs		0/1
5	Low Temperature Storage	TEMP. : -40°C	1000hrs	22pcs		0/1
6	DC Operating Life	V <sub>CE</sub> =5V	1000hrs	22pcs		0/1
7	High Temperature/ High Humidity	85°C / 85% R.H	1000hrs	22pcs		0/1

